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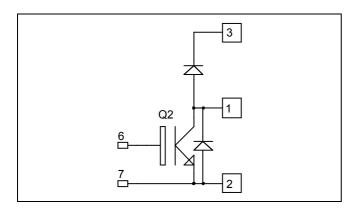
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Boost chopper NPT IGBT Power Module

$$V_{CES} = 600V$$

 $I_{C} = 330A$ @ $T_{C} = 80^{\circ}C$



Application • AC

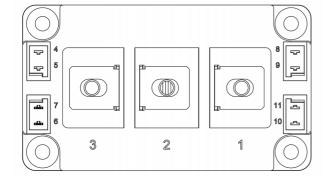
- AC and DC motor control
- Switched Mode Power Supplies
- Power Factor Correction

Features

- Non Punch Through (NPT) FAST IGBT
 - Low voltage drop
 - Low tail current
 - Switching frequency up to 50 kHz
 - Soft recovery parallel diodes
 - Low diode VF
 - Low leakage current
 - RBSOA and SCSOA rated
- Kelvin emitter for easy drive
- High level of integration
- M6 power connectors

Benefits

- Stable temperature behavior
- Very rugged
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Easy paralleling due to positive T_C of V_{CEsat}
- RoHS Compliant



Absolute maximum ratings

Symbol	Parameter		Max ratings	Unit
V_{CES}	Collector - Emitter Breakdown Voltage		600	V
$I_{\rm C}$	Continuous Collector Current	$T_C = 25^{\circ}C$	520	
	Continuous Conector Current	$T_C = 80$ °C	330	A
I_{CM}	Pulsed Collector Current	$T_C = 25^{\circ}C$	800	
V_{GE}	Gate – Emitter Voltage		±20	V
P_{D}	Maximum Power Dissipation	$T_C = 25$ °C	1560	W
RBSOA	Reverse Bias Safe Operating Area	$T_j = 125^{\circ}C$	800A @ 520V	

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com



All ratings @ $T_j = 25$ °C unless otherwise specified

Electrical Characteristics

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
I_{CES}	Zero Gate Voltage Collector Current	$V_{GE} = 0V, V_{CE} = 600V$				500	μA
V _{CE(sat)}	Collector Emitter saturation Voltage	, GE 10 ,	$T_j = 25^{\circ}C$		1.95	2.45	V
			$T_j = 125$ °C		2.2		·
$V_{GE(th)}$	Gate Threshold Voltage	$V_{GE} = V_{CE}, I_C = 7.5 \text{ mA}$		5.0	5.8	6.5	V
I_{GES}	Gate – Emitter Leakage Current	$V_{GE} = 20V, V_{CE} = 0V$				1200	nA

Dynamic Characteristics

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
Cies	Input Capacitance	$V_{GE} = 0V ; V_{CE} = 25V$ $f = 1MHz$			18		nF
C_{res}	Reverse Transfer Capacitance				1.6		
Q_{G}	Gate charge	V _{GE} =15V, I _C =400A V _{CE} =300V			1.3		μС
$T_{d(on)}$	Turn-on Delay Time	Inductive Switch	ing (25°C)		150		
$T_{\rm r}$	Rise Time	$V_{GE} = \pm 15V$			72		
$T_{d(off)}$	Turn-off Delay Time	$V_{\text{Bus}} = 300V$ $I_{\text{C}} = 400A$ $R_{\text{G}} = 8\Omega$			530		ns
T_{f}	Fall Time				40		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (125°C) $V_{GE} = \pm 15V$ $V_{Bus} = 300V$ $I_{C} = 400A$ $R_{G} = 8\Omega$			160		ns
T_{r}	Rise Time				75		
$T_{d(off)}$	Turn-off Delay Time				550		
$T_{\rm f}$	Fall Time				50		
Eon	Turn on Energy	$V_{GE} = \pm 15V$ $V_{Bus} = 300V$	$T_j = 125$ °C		18		mJ
E_{off}	Turn off Energy	$I_{C} = 400A$ $R_{G} = 8\Omega$	$T_j = 125$ °C		17		1110
I_{sc}	Short Circuit data	$V_{GE} \le 15V$; $V_{Bus} = 360V$ $t_p \le 10 \mu s$; $T_i = 125 ^{\circ}C$			1800		A

Reverse diode ratings and characteristics

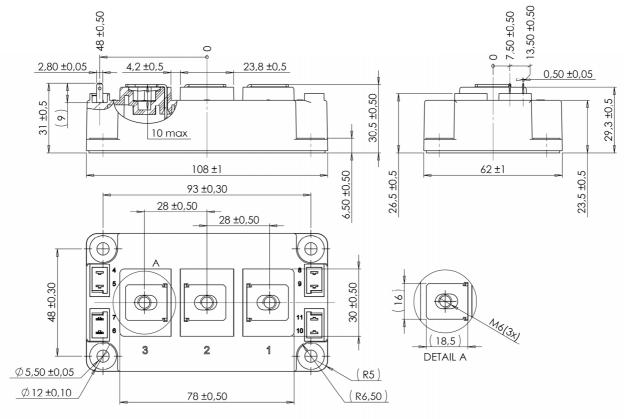
Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
V_{RRM}	Maximum Peak Repetitive Reverse Voltage			600			V
I_{RRM}	Maximum Reverse Leakage Current	$V_R = 600V$	$T_i = 25^{\circ}C$			750	μΑ
I_{F}	DC Forward Current		$T_{j} = 125^{\circ}C$ $Tc = 80^{\circ}C$		400	1000	A
V	Diode Forward Voltage	$I_F = 400A$ $V_{GE} = 0V$	$T_i = 25^{\circ}C$		1.25	1.6	V
V_{F}			$T_i = 125^{\circ}C$		1.2		
+	Reverse Recovery Time	$I_F = 400A$ $V_R = 300V$ $di/dt = 4400A/\mu s$	$T_j = 25^{\circ}C$		150		ns
t_{rr}			$T_j = 125$ °C		250		
Q _{rr}	Reverse Recovery Charge		$T_i = 25^{\circ}C$		27		
			$T_j = 125$ °C		44		μC
E _{rr}	Reverse Recovery Energy	αι/αι 1100/1/μ3	$T_i = 25^{\circ}C$		5.6		ma T
			$T_{i} = 125^{\circ}C$		9.2		mJ



Thermal and package characteristics

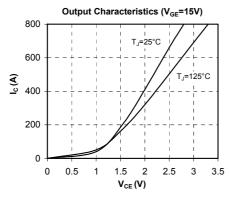
Symbol	Characteristic			Min	Тур	Max	Unit
D	Junction to Case Thermal Resistance		IGBT			0.08	°C/W
R _{thJC} Junction to Case Thermal Resistan		Diode				0.15	C/ VV
V_{ISOL}	RMS Isolation Voltage, any terminal to case t = 1 min, 50/60Hz			4000			V
T_{J}	Operating junction temperature range	Operating junction temperature range		-40		150	
T_{STG}	Storage Temperature Range		-40		125	°C	
$T_{\rm C}$	Operating Case Temperature			-40		125	
Torque	Mounting forque	For terminals	M6	3		5	N.m
		To Heatsink	M6	3		5	18.111
Wt	Package Weight					350	g

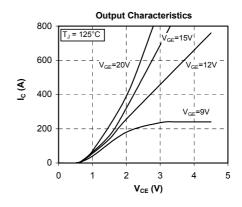
D3 Package outline (dimensions in mm)

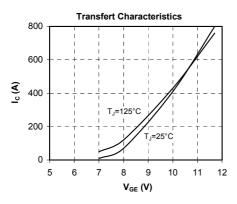


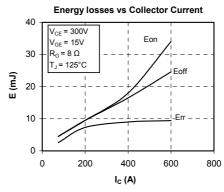


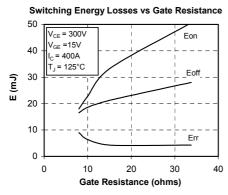
Typical Performance Curve

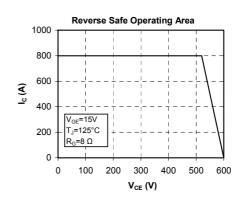


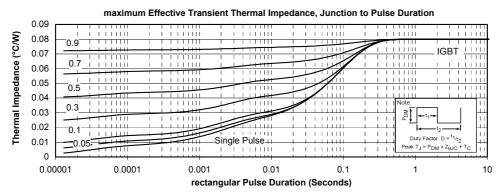








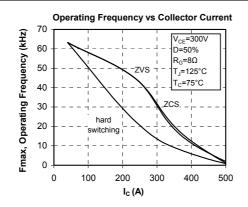


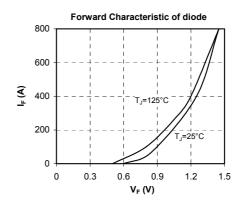


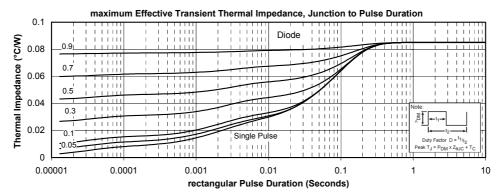
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